

20V P-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max @ T _A = +25°C (Note 5)
-20V	495mΩ @ V _{GS} = -4.5V	-0.77A
	690mΩ @ V _{GS} = -2.5V	-0.67A
	960mΩ @ V _{GS} = -1.8V	-0.57A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

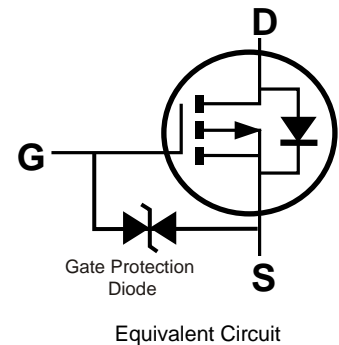
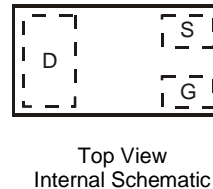
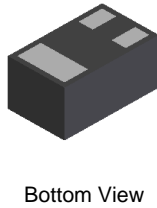
- Portable Electronics

Features and Benefits

- Footprint of Just 0.6mm² – Thirteen Times Smaller Than SOT23
- Low Gate Threshold Voltage
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **ESD Protected Gate 3kV**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.001 grams (Approximate)


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP21D0UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

X1-DFN1006-3



NG = Product Type Marking Code

Top View
Bar Denotes Gate
and Source Side

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current	Steady State $V_{GS} = -4.5\text{V}$	$T_A = +25^\circ\text{C}$ (Note 5)	I_D	-0.77	A
		$T_A = +85^\circ\text{C}$ (Note 5)		-0.55	
		$T_A = +25^\circ\text{C}$ (Note 6)		-1.17	
Pulsed Drain Current (Note 7)			I_{DM}	-5.0	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	0.43	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	293	$^\circ\text{C/W}$
Power Dissipation (Note 6)	P_D	0.99	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	126	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

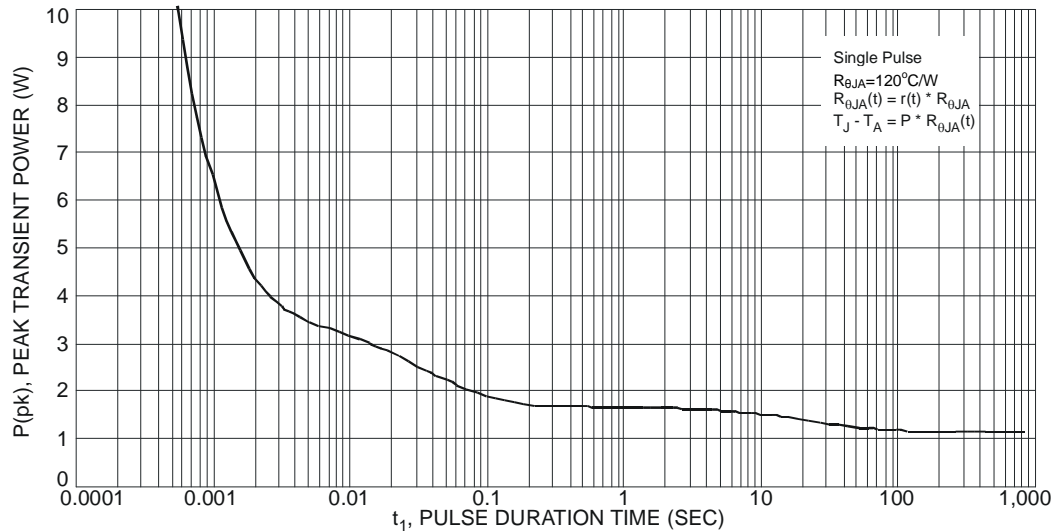
Thermal Characteristics


Fig. 1 Single Pulse Maximum Power Dissipation

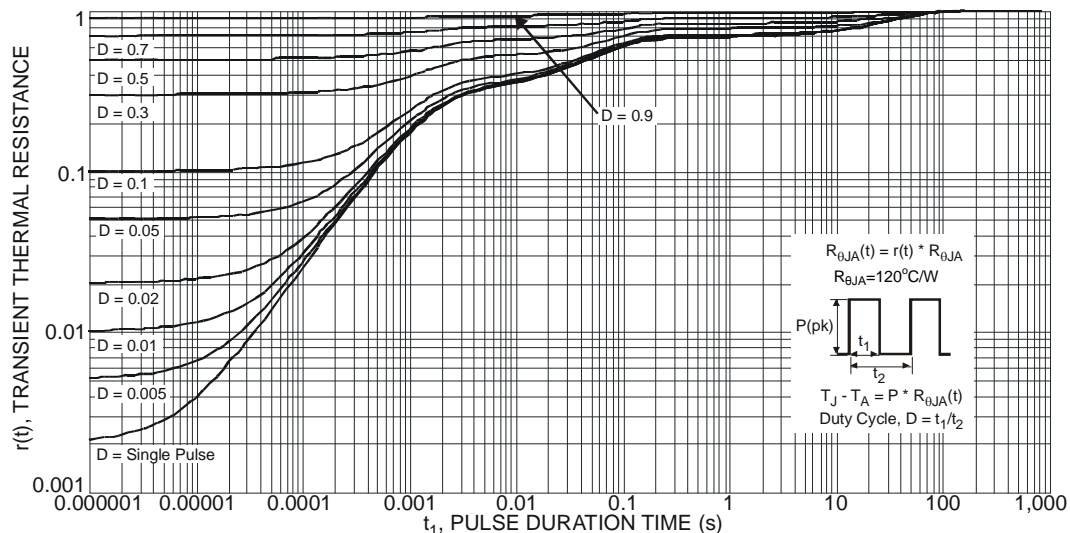


Fig. 2 Transient Thermal Response

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	-	-	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	-0.7	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	495	mΩ	V _{GS} = -4.5V, I _D = -400mA
				690		V _{GS} = -2.5V, I _D = -300mA
				960		V _{GS} = -1.8V, I _D = -100mA
Forward Transfer Admittance	Y _{fs}	50	-	-	mS	V _{DS} = -3V, I _D = -300mA
Diode Forward Voltage	V _{SD}	-	-	-1.2	V	V _{GS} = 0V, I _S = -300mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	-	76.5	-	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	13.7	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	10.7	-	pF	
Gate Resistance	R _g	-	195	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	1.5	-	nC	V _{GS} = -8V, V _{DS} = -15V, I _D = -1A
Total Gate Charge	Q _g	-	1.0	-	nC	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -1A
Gate-Source Charge	Q _{gs}	-	0.2	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.3	-	nC	
Turn-On Delay Time	t _{D(ON)}	-	7.1	-	ns	V _{DS} = -10V, I _D = -1A V _{GS} = -4.5V, R _G = 6Ω
Turn-On Rise Time	t _R	-	8.0	-	ns	
Turn-Off Delay Time	t _{D(OFF)}	-	31.7	-	ns	
Turn-Off Fall Time	t _F	-	18.5	-	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1 inch square copper plate.
 - Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

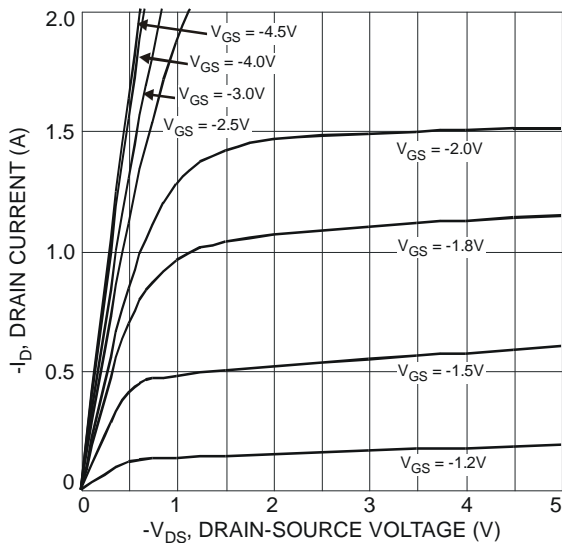
Typical Characteristics


Fig. 3 Typical Output Characteristic

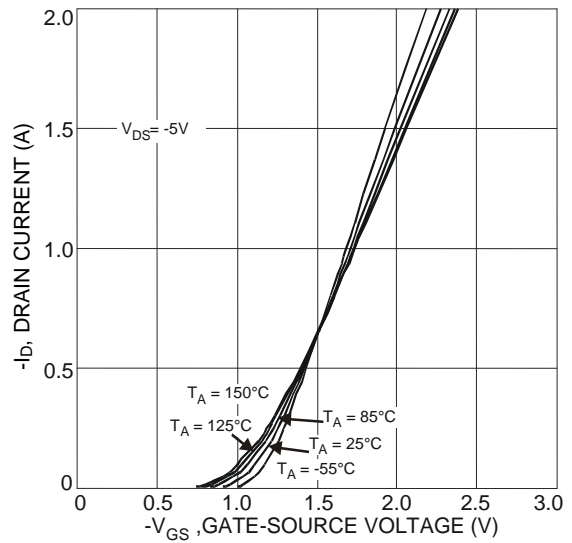


Fig. 4 Typical Transfer Characteristic

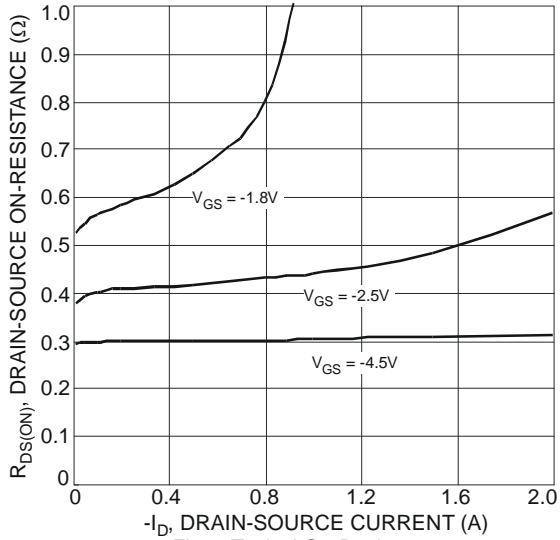


Fig. 5 Typical On-Resistance vs. Drain Current and Gate Voltage

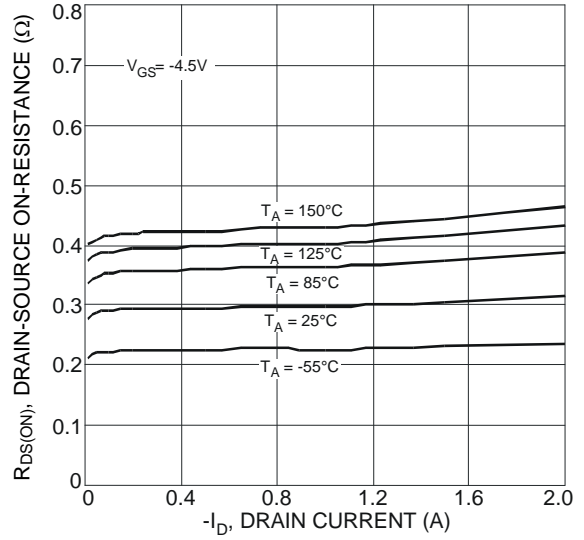


Fig. 6 Typical On-Resistance vs. Drain Current and Temperature

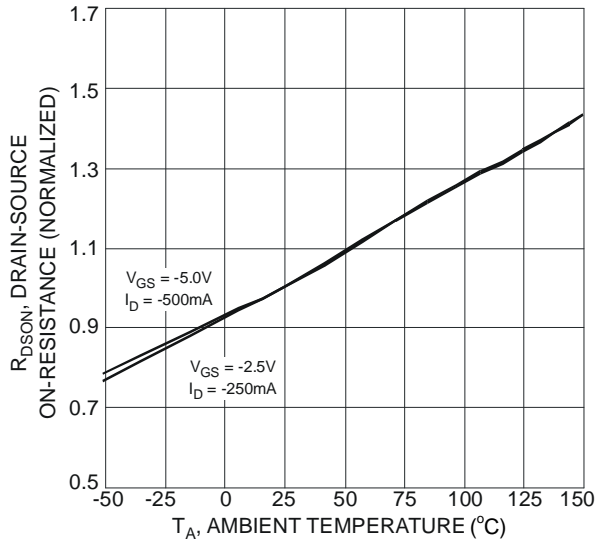


Fig. 7 On-Resistance Variation with Temperature

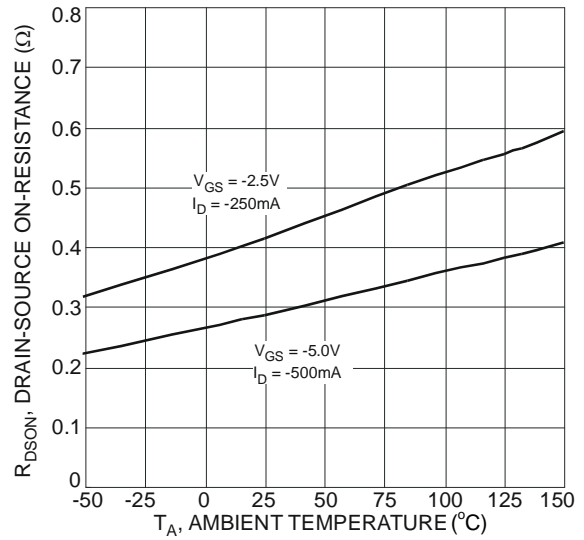


Fig. 8 On-Resistance Variation with Temperature

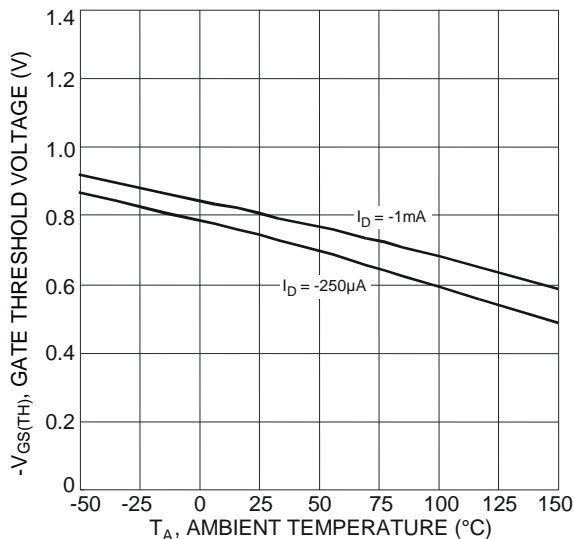


Fig. 9 Gate Threshold Variation vs. Ambient Temperature

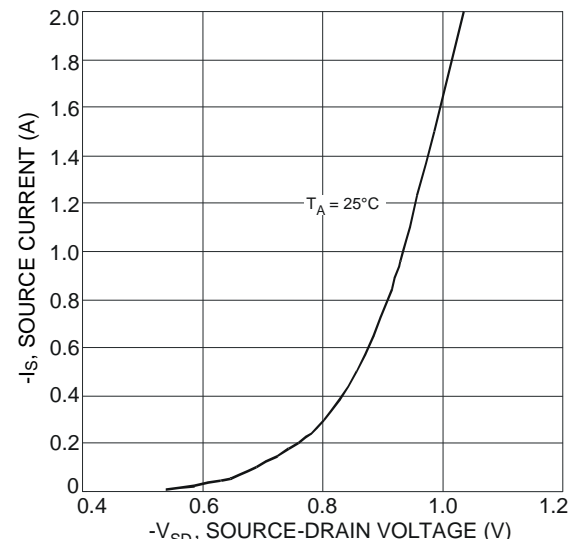


Fig. 10 Diode Forward Voltage vs. Current

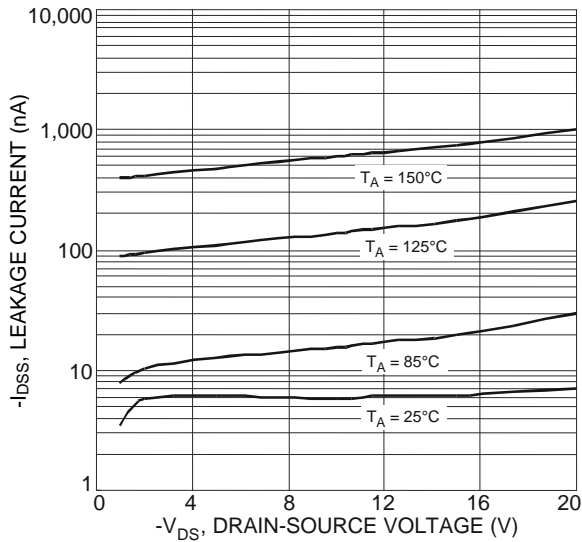


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage

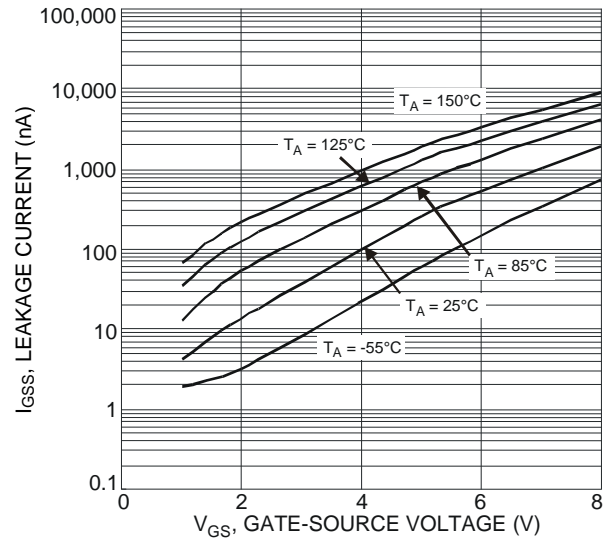


Fig. 12 Leakage Current vs. Gate-Source Voltage

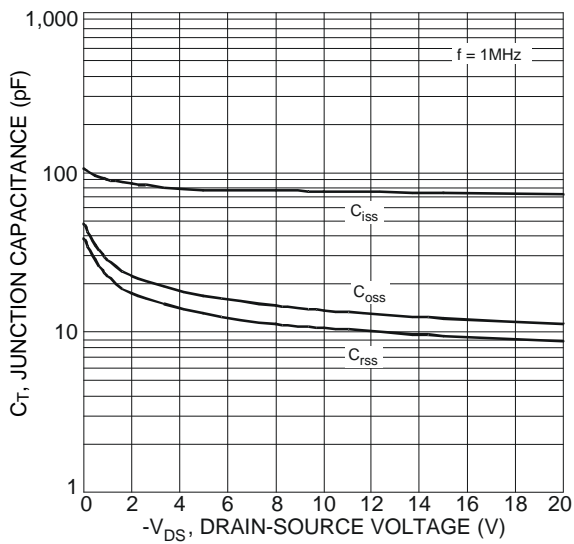


Fig. 13 Typical Junction Capacitance

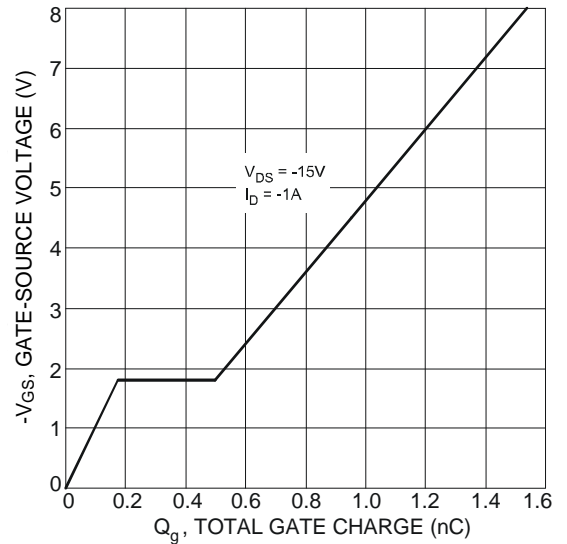


Fig. 14 Gate-Charge Characteristics

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